

Title (en)
SiC SINGLE CRYSTAL AND METHOD FOR GROWING THE SAME

Title (de)
SiC-EINKRISTALL UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)
MONOCRISTAL EN SiC ET SON PROCEDE DE CROISSANCE

Publication
EP 1249521 B8 20060503 (EN)

Application
EP 00956968 A 20000906

Priority
• JP 0006057 W 20000906
• JP 36459399 A 19991222

Abstract (en)
[origin: EP1249521A1] The growth of a silicon carbide single crystal comprises growing a SiC single crystal on a seed crystal comprising a SiC single crystal at an angle α (20 [deg] less than α less than 60 [deg]) to the {0001} surface and at an angle β of ≈ 15 [deg] of the vector obtained by projecting the normal vector onto the {0001} surface and the (11-20) direction. An independent claim is also included for a silicon carbide single crystal grown by this method.

IPC 8 full level
C30B 23/00 (2006.01); **C30B 23/02** (2006.01); **C30B 25/00** (2006.01); **C30B 25/02** (2006.01); **C30B 25/20** (2006.01); **C30B 29/36** (2006.01); **H01L 21/205** (2006.01)

CPC (source: EP)
C30B 23/00 (2013.01); **C30B 23/005** (2013.01); **C30B 25/00** (2013.01); **C30B 29/36** (2013.01)

Cited by
EP1403404A4; CN102337587A; EP1639158A4; DE10247017B4; US2007221119A1; US9059118B2; WO2005111277A1; US7637998B2; US7527869B2; US8147991B2; US9200381B2; US9790619B2

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